PROCESS CPD38X

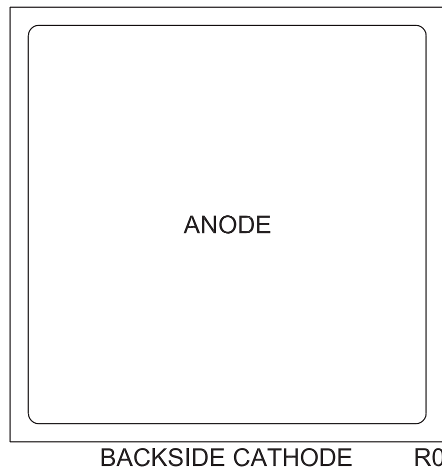
Schottky Rectifier

8 Amp Schottky Rectifier Chip

PROCESS DETAILS

Die Size	72 x 72 MILS
Die Thickness	5.9 MILS
Anode Bonding Pad Area	64 x 64 MILS
Top Side Metalization	Al/Ni/Au - 30,000Å/4,000Å/1,500Å
Back Side Metalization	Ti/Ni/Au - 1,600Å/5,550Å/1,500Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER
3,137

R1 (29-April 2010)